

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	0	(FET or Field near effect near transistor) and (high near power) and (channel near regions) and (perpendicular near width) and (bent near agte near electro	USPAT; JPO; DERWE NT	2001/08/13 14:56
2	BRS	L2	0	(FET or Field near effect near transistor) and (high near power) and (channel near regions) and (bent near agte near electrodes)	USPAT; JPO; DERWE NT	2001/08/13 15:06
3	BRS	L3	0	(FET or Field near effect near transistor) and (high near power) and (bent near gate near	USPAT; JPO; DERWE NT	2001/08/13 15:00
4	BRS	L4	1	(FET or Field near effect near transistor) and (bent near gate near electrodes)	USPAT; JPO; DERWE NT	2001/08/13 15:06
5	BRS	L5	680	(FET or Field near effect near transistor) and (high near power) and (channel near regions)	USPAT; JPO; DERWE NT	2001/08/13 15:08
6	BRS	L6	4	(FET or Field near effect near transistor) and (high near power) and (channel near regions)	USPAT; JPO; DERWE NT	2001/08/13 15:08